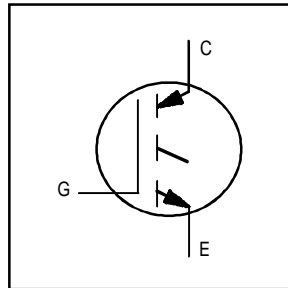




IRG4CC50WB IGBT Die in Wafer Form

IRG4CC50WB



600 V
Size 5
WARP Speed
6" Wafer

Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	2.3V Max.	$I_C = 10A, T_J = 25^\circ C, V_{GE} = 15V$
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600V Min.	$T_J = 25^\circ C, I_{CES} = 250\mu A, V_{GE} = 0V$
$V_{GE(th)}$	Gate Threshold Voltage	3.0V Min., 6.0V Max.	$V_{GE} = V_{CE}, T_J = 25^\circ C, I_C = 250\mu A$
I_{CES}	Zero Gate Voltage Collector Current	250 μA Max.	$T_J = 25^\circ C, V_{CE} = 600V$
I_{GES}	Gate-to-Emitter Leakage Current	$\pm 1.1 \mu A$ Max.	$T_J = 25^\circ C, V_{GE} = \pm 20V$

Mechanical Data

Nominal Backmetal Composition, Thickness:	Cr-NiV-Ag (1kA-2kA-.2.5kA)
Nominal Front Metal Composition, Thickness:	99% Al, 1% Si (4 microns)
Dimensions:	0.257" x 0.260"
Wafer Diameter:	150mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5226
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	Consistent throughout same wafer lot
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions	For optimum electrical results, die attach temperature should not exceed 300C

Reference Standard IR packaged part (for design) : IRG4PC50W

Die Outline

